

**KJ10N20K**

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### Features

- Self-aligned Planar Technology
- Excellent Switching Performance

#### Applications

- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

#### Quick reference

$V_{DS} = 200V$

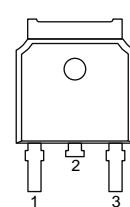
$I_D = 10A$

$R_{DS(ON)} \leq 0.3\Omega$  @  $V_{GS}=10V$  (Type:0.23Ω)

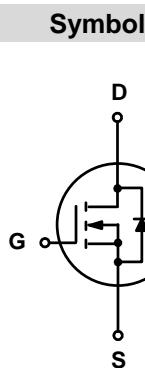
#### Pin Description

Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

#### Simplified Outline



Top View  
TO-252-3L



#### Package Marking and Ordering Information

Product Name	Package	Marking		Reel Size	Tape Width	Quantity
KJ10N20K	TO-252-3L	10N20	XXXXYY: Date Code	-	-	2500

### 2. Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Values	Unit
$V_{DS}$	Drain-Source Voltage	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current, $V_{GS}@10V$	10	A
$I_{DM}$	Pulsed Drain Current	36	A
$E_{AS}$	Single Pulse Avalanche Energy	100	mJ
$I_{AR}$	Avalanche Current	7.5	A
$E_{AR}$	Repetitive Avalanche Energy	8.1	mJ
$P_D@T_C=25^\circ C$	Power Dissipation	74	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55~+150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	1.7	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	60	°C/W

### 3. Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	200	-	-	V
$I_{GSS}$	Gate-body Leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$	-	-	$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current, $T_J=25^\circ\text{C}$	$V_{DS}=200\text{V}$ , $V_{GS}=0\text{V}$	-	-	5	$\mu\text{A}$
$I_{DSS}$	Zero Gate Voltage Drain Current, $T_J=125^\circ\text{C}$	$V_{DS}=160\text{V}$ , $V_{GS}=0\text{V}$	-	-	100	
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1.2	-	2.5	V
$R_{DS(on)}$	Drain-Source on-Resistance	$V_{GS}=10\text{V}$ , $I_D=4.5\text{A}$	-	0.23	0.3	$\Omega$
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$	-	684	-	pF
$C_{oss}$	Output Capacitance		-	103	-	
$C_{rss}$	Reverse Transfer Capacitance		-	37	-	
$Q_g$	Total Gate Charge	$V_{GS}=10\text{V}$ , $V_{DS}=160\text{V}$ , $I_D=10\text{A}$	-	23	-	nC
$Q_{gs}$	Gate-Source Charge		-	2.5	-	
$Q_{gd}$	Gate-Drain Charge		-	10	-	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=10\text{V}$ , $V_{DS}=100\text{V}$ , $R_G=25\Omega$ , $I_D=10\text{A}$	-	12	-	ns
$t_r$	Turn-on Rise Time		-	22	-	
$t_{d(off)}$	Turn-off Delay Time		-	50	-	
$t_f$	Turn-off Fall Time		-	48	-	
$I_s$	Continuous Source Current	$T_C=25^\circ\text{C}$	-	-	9	A
$I_{SM}$	Pulsed Diode Forward Current		-	-	36	A
$V_{SD}$	Diode Forward Voltage	$T_J=25^\circ\text{C}$ , $I_{SD}=10\text{A}$ , $V_{GS}=0\text{V}$	-	-	1.4	V
$t_{rr}$	Body Diode Reverse Recovery Time	$V_{GS}=0\text{V}$ , $I_S=10\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$	-	190	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	1.7	-	nC

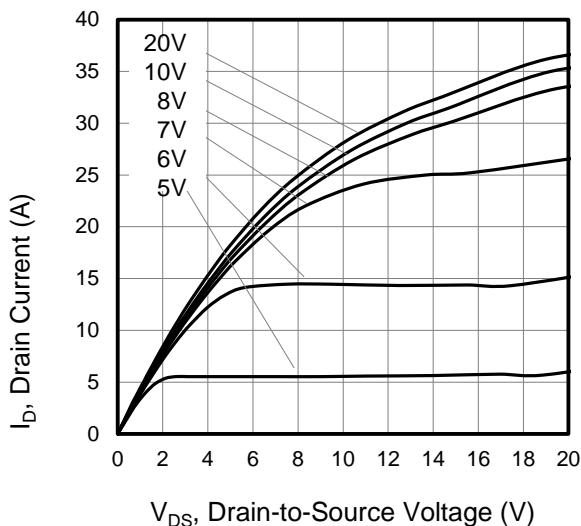
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature

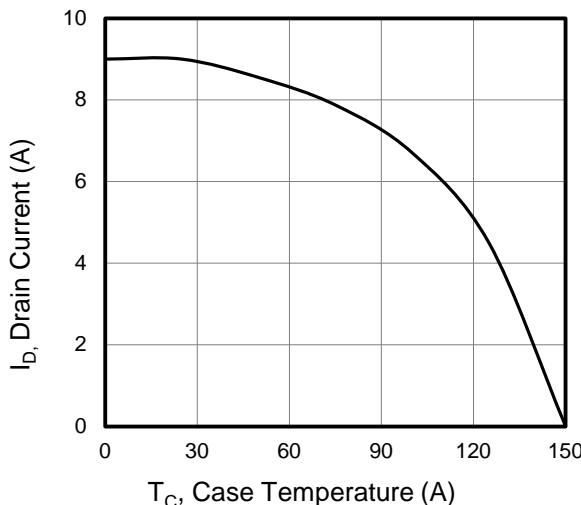
2.  $I_{AS}=7.5\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$

3. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

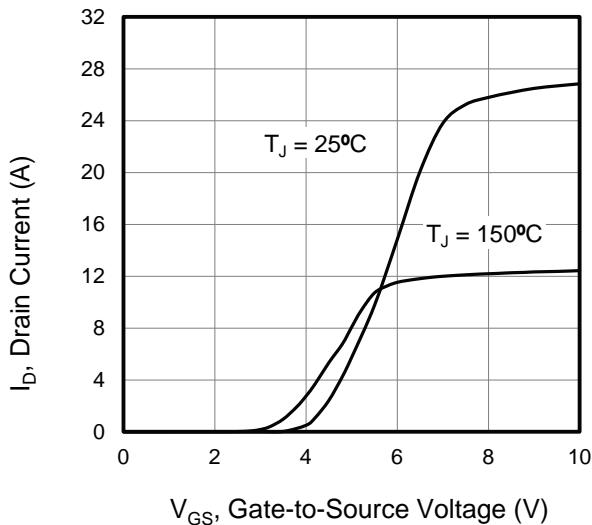
#### 4.Typical Characteristics



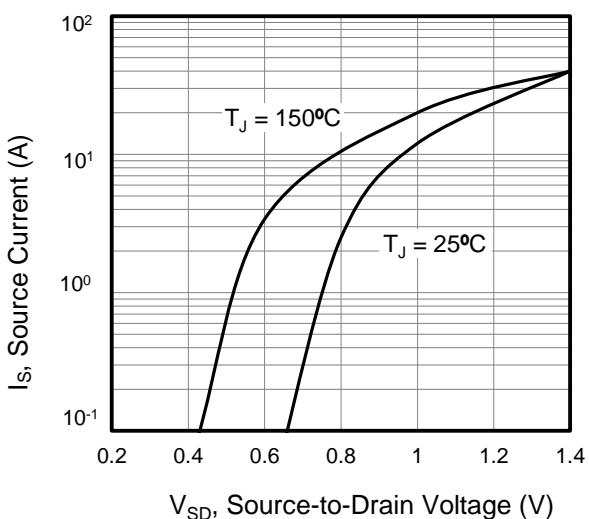
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



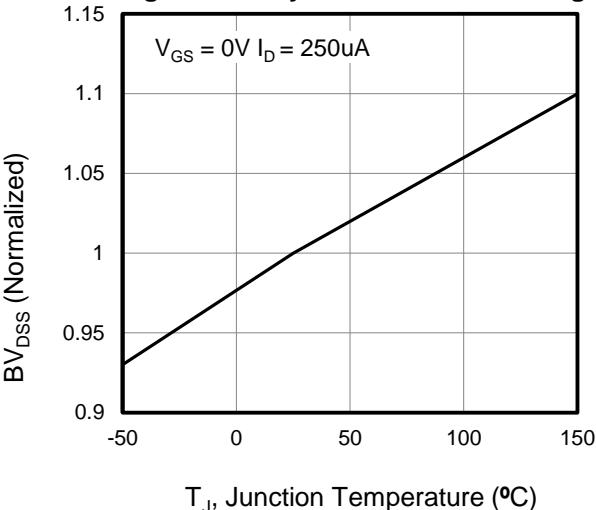
**Figure 3. Drain Current vs. Temperature**



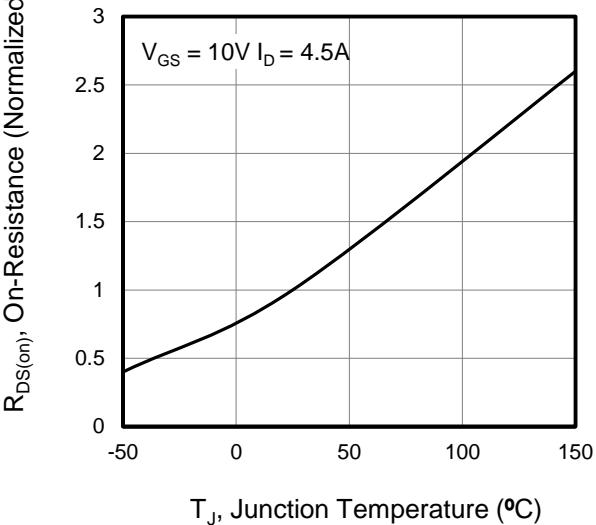
**Figure 5. Transfer Characteristics**



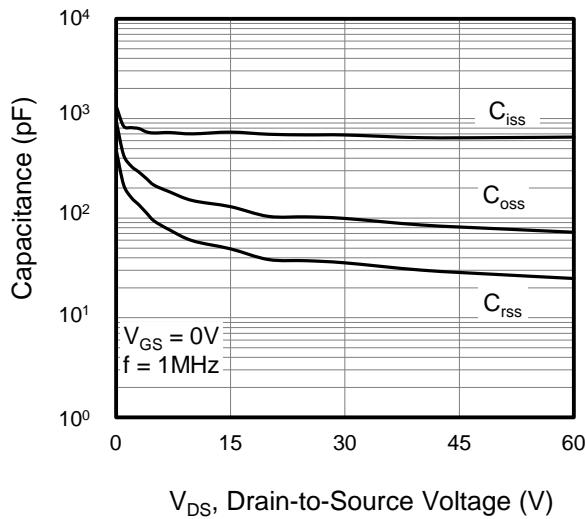
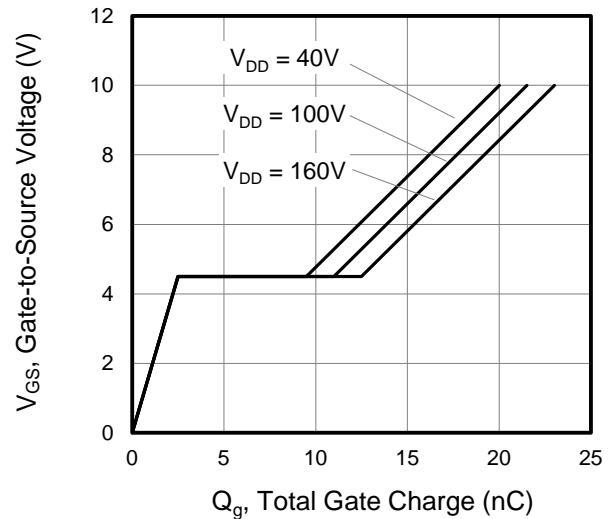
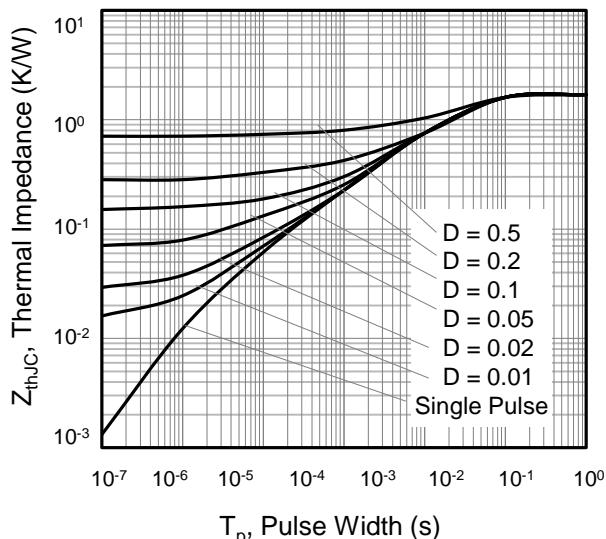
**Figure 2. Body Diode Forward Voltage**

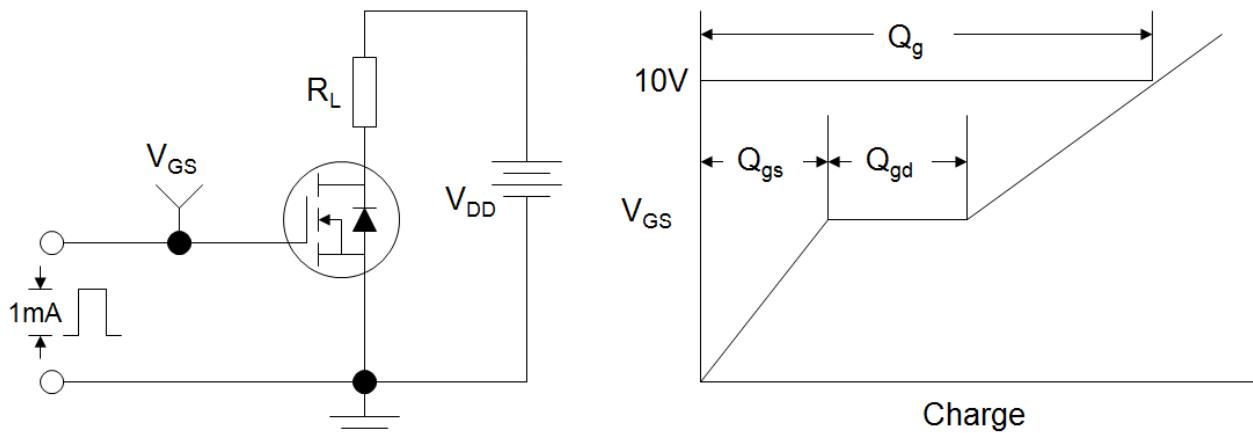


**Figure 4.  $BV_{DSS}$  Variation vs. Temperature**

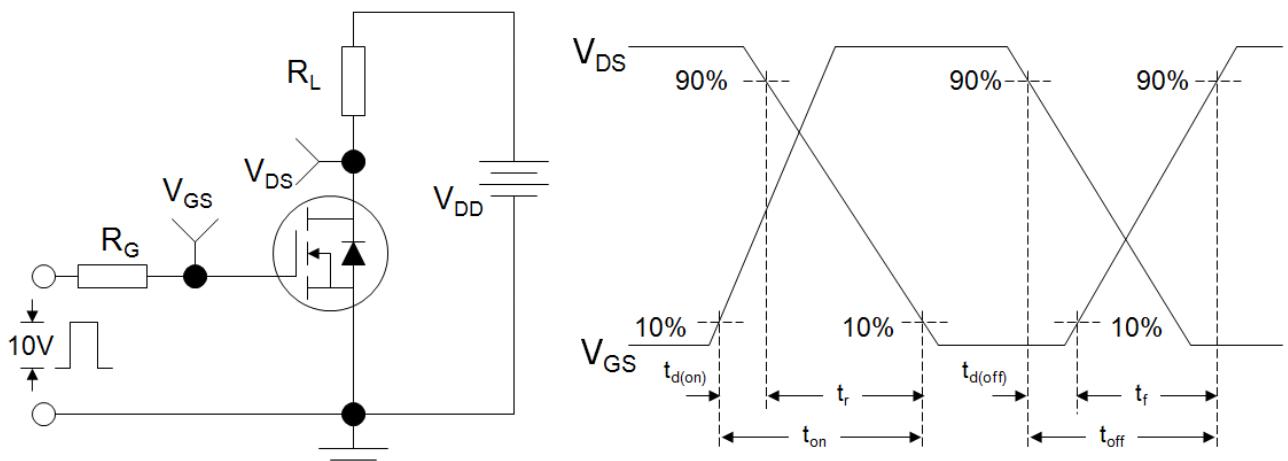


**Figure 6. On-Resistance vs. Temperature**

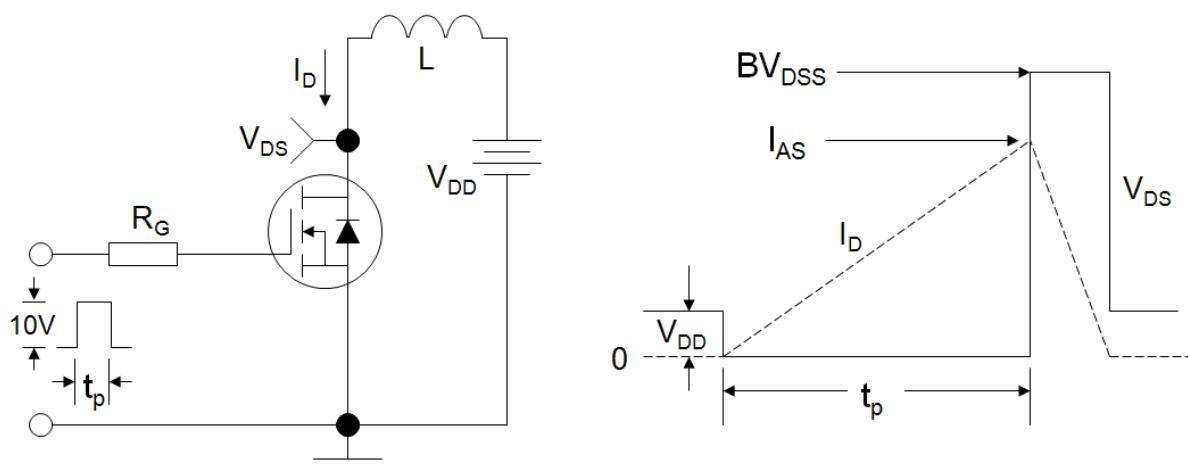

**Figure 7. Capacitance**

**Figure 8. Gate Charge**

**Figure 10. Transient Thermal Impedance**



**Figure A: Gate Charge Test Circuit and Waveform**



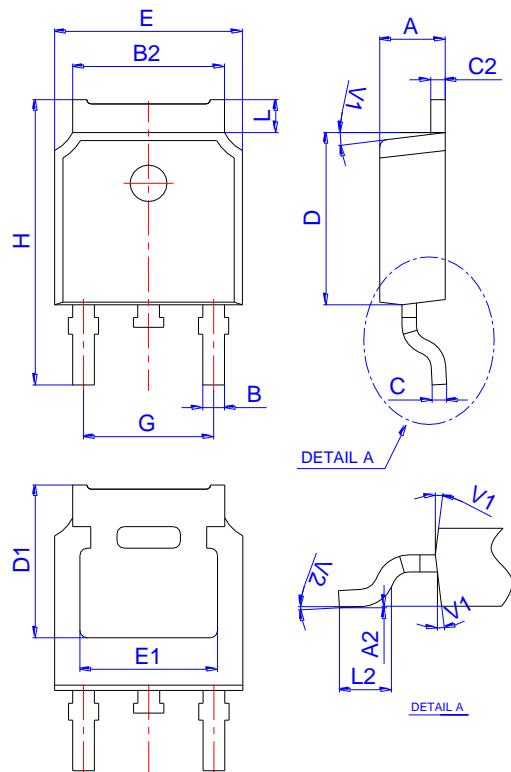
**Figure B: Resistive Switching Test Circuit and Waveform**



**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**

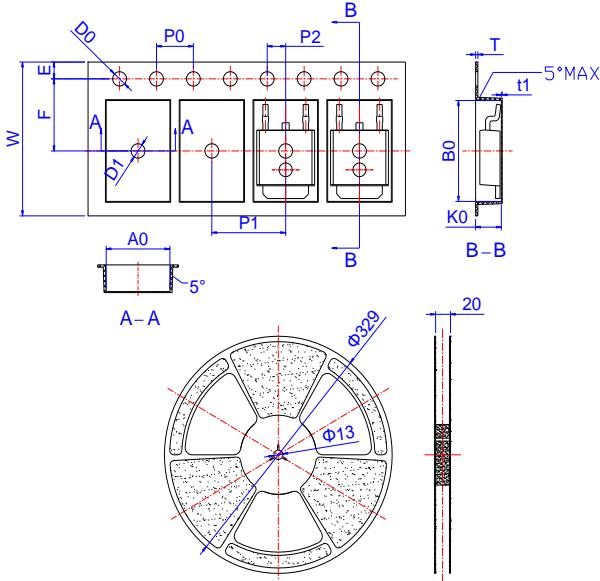
## 5.Package Mechanical Data

**TO-252-3L**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

## Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583